

**Effective Solution and Process to Wet-Etch metal-alloy
films in Semiconductor Processing**

5 ABSTRACT OF THE INVENTION

A solution and method is described for etching TaN, TiN, Cu, FSG, TEOS, and SiN on a silicon substrate in silicon device processing. The solution is formed by combining HF at 49% concentration with H₂O₂ at 29%-30%
10 concentration in deionized water.